

2SK3156

Silicon N Channel MOS FET High Speed Power Switching

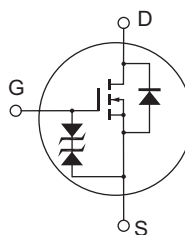
REJ03G1081-0300
(Previous: ADE-208-683A)
Rev.3.00
Sep 07, 2005

Features

- Low on-resistance
 $R_{DS} = 50 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

RENESAS Package code: PRSS0004AC-A
(Package name: TO-220AB)



1. Gate
2. Drain
(Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	150	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	20	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	80	A
Body-drain diode reverse drain current	I_{DR}	20	A
Avalanche current	I_{AP} ^{Note3}	20	A
Avalanche energy	E_{AR} ^{Note3}	30	mJ
Channel dissipation	P_{ch} ^{Note2}	75	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Notes: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$ 2. Value at $T_c = 25^\circ C$ 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50\ \Omega$

Electrical Characteristics

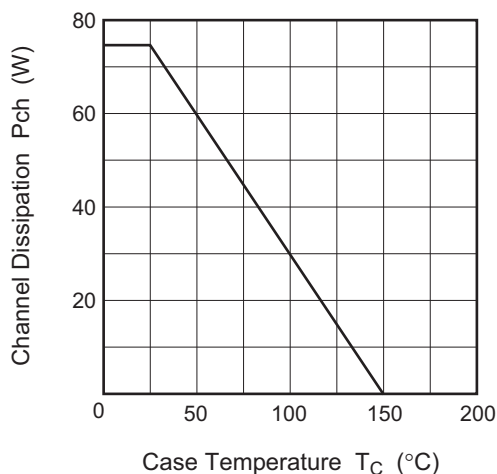
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 10\text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\ \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 150\text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1\text{ mA}$, $V_{DS} = 10\text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	50	70	mΩ	$I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	60	80	mΩ	$I_D = 10\text{ A}$, $V_{GS} = 4\text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	13	22	—	S	$I_D = 10\text{ A}$, $V_{DS} = 10\text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1750	—	pF	$V_{DS} = 10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Output capacitance	C_{oss}	—	600	—	pF	
Reverse transfer capacitance	C_{rss}	—	300	—	pF	
Turn-on delay time	$t_{d(on)}$	—	18	—	ns	$I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$, $R_L = 3\ \Omega$
Rise time	t_r	—	125	—	ns	
Turn-off delay time	$t_{d(off)}$	—	400	—	ns	
Fall time	t_f	—	190	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 20\text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	170	—	ns	$I_F = 20\text{ A}$, $V_{GS} = 0$ $di_F/dt = 50\text{ A}/\mu s$

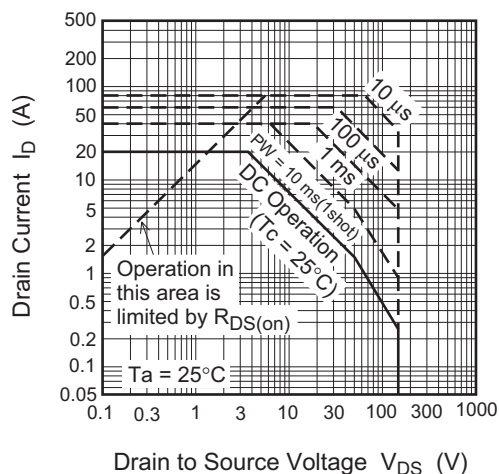
Note: 4. Pulse test

Main Characteristics

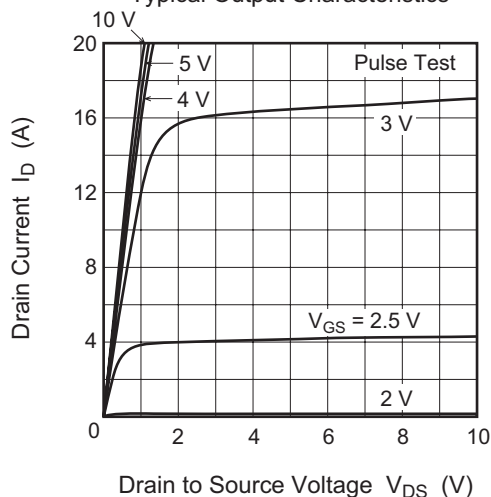
Power vs. Temperature Derating



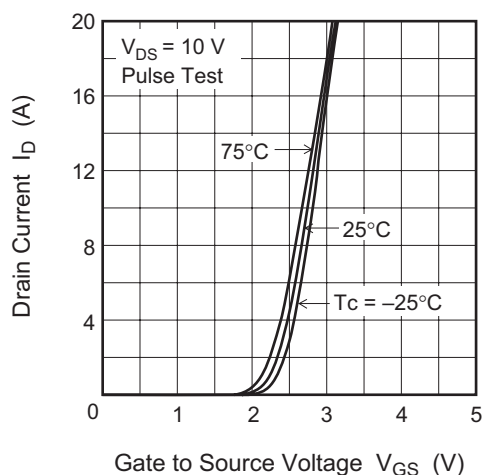
Maximum Safe Operation Area



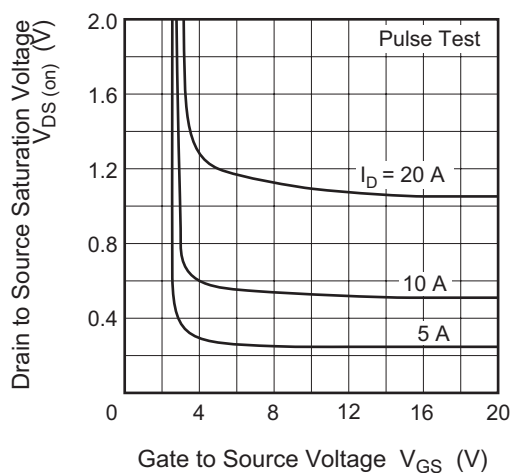
Typical Output Characteristics



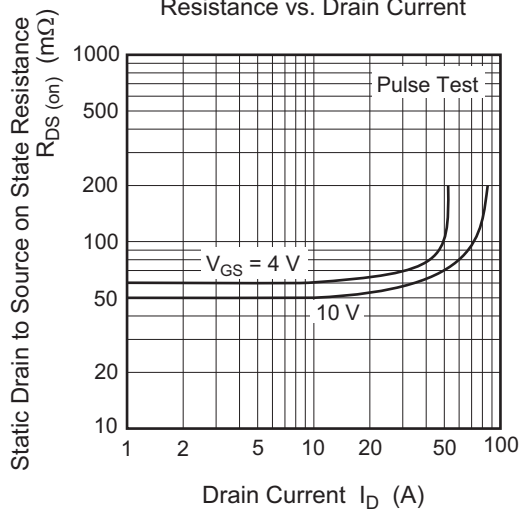
Typical Transfer Characteristics

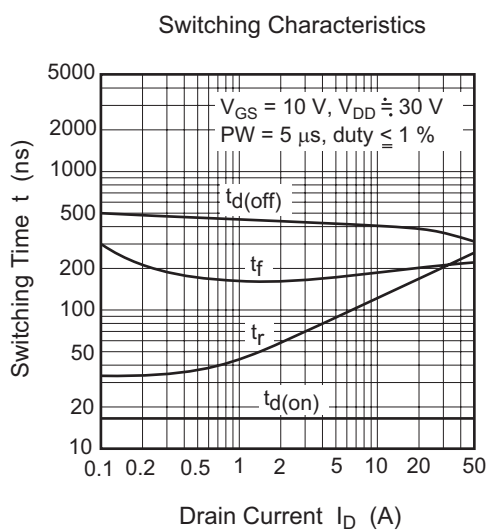
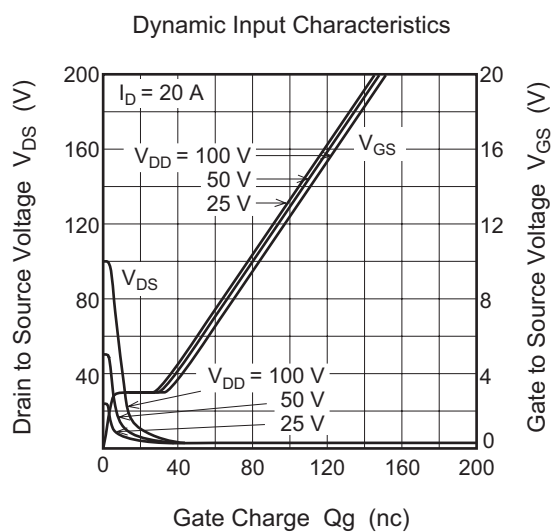
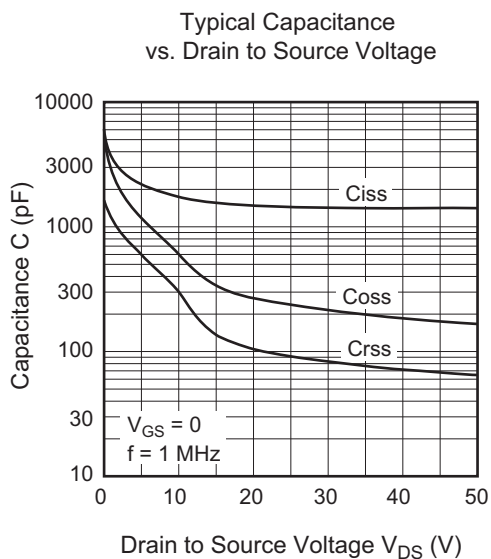
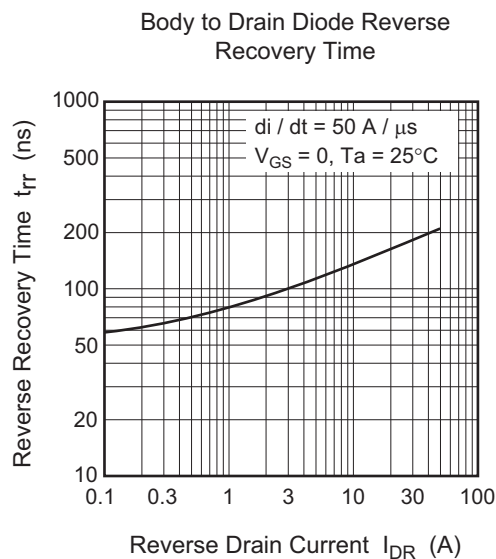
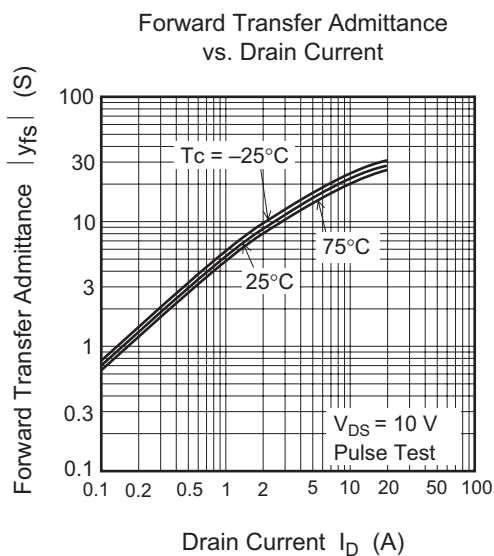
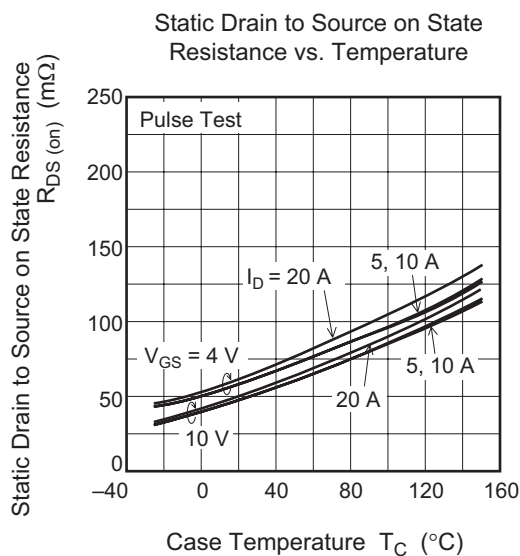


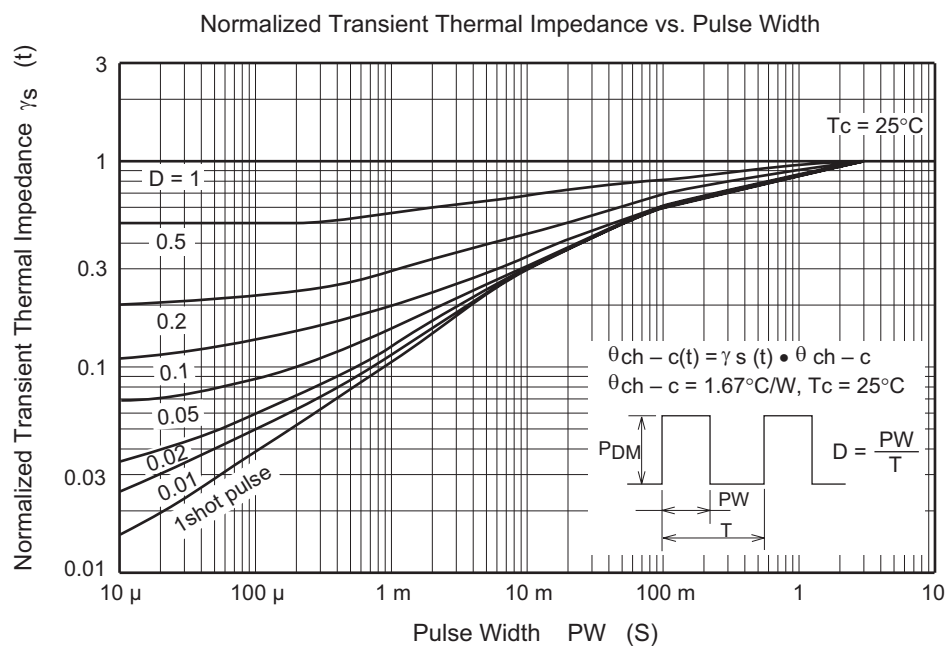
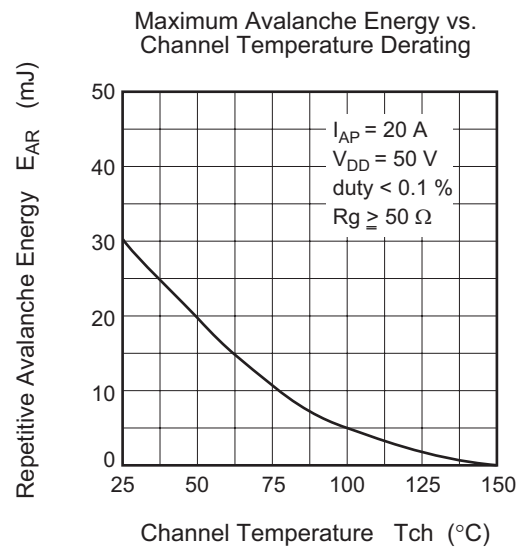
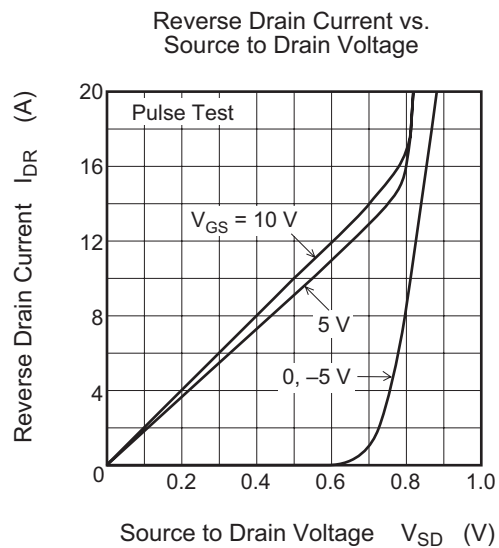
Drain to Source Saturation Voltage vs. Gate to Source Voltage



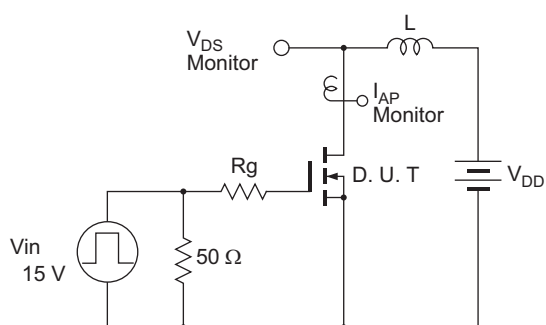
Static Drain to Source on State Resistance vs. Drain Current





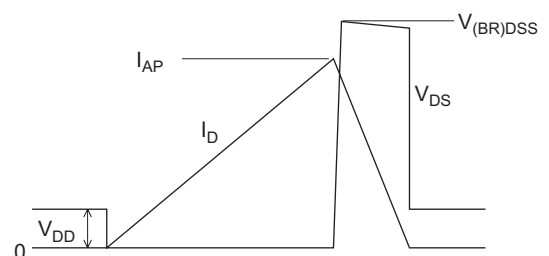


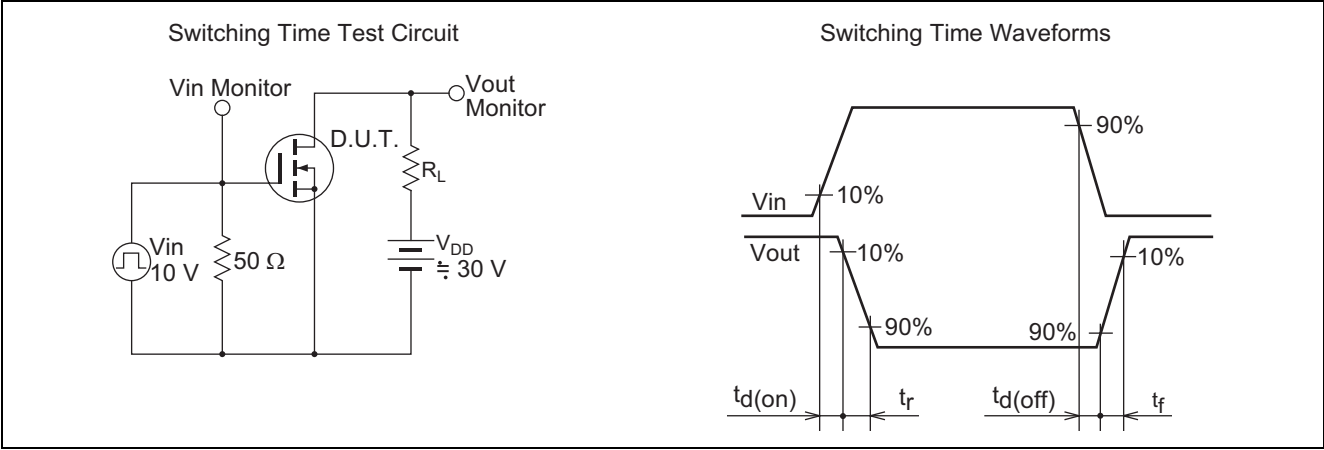
Avalanche Test Circuit



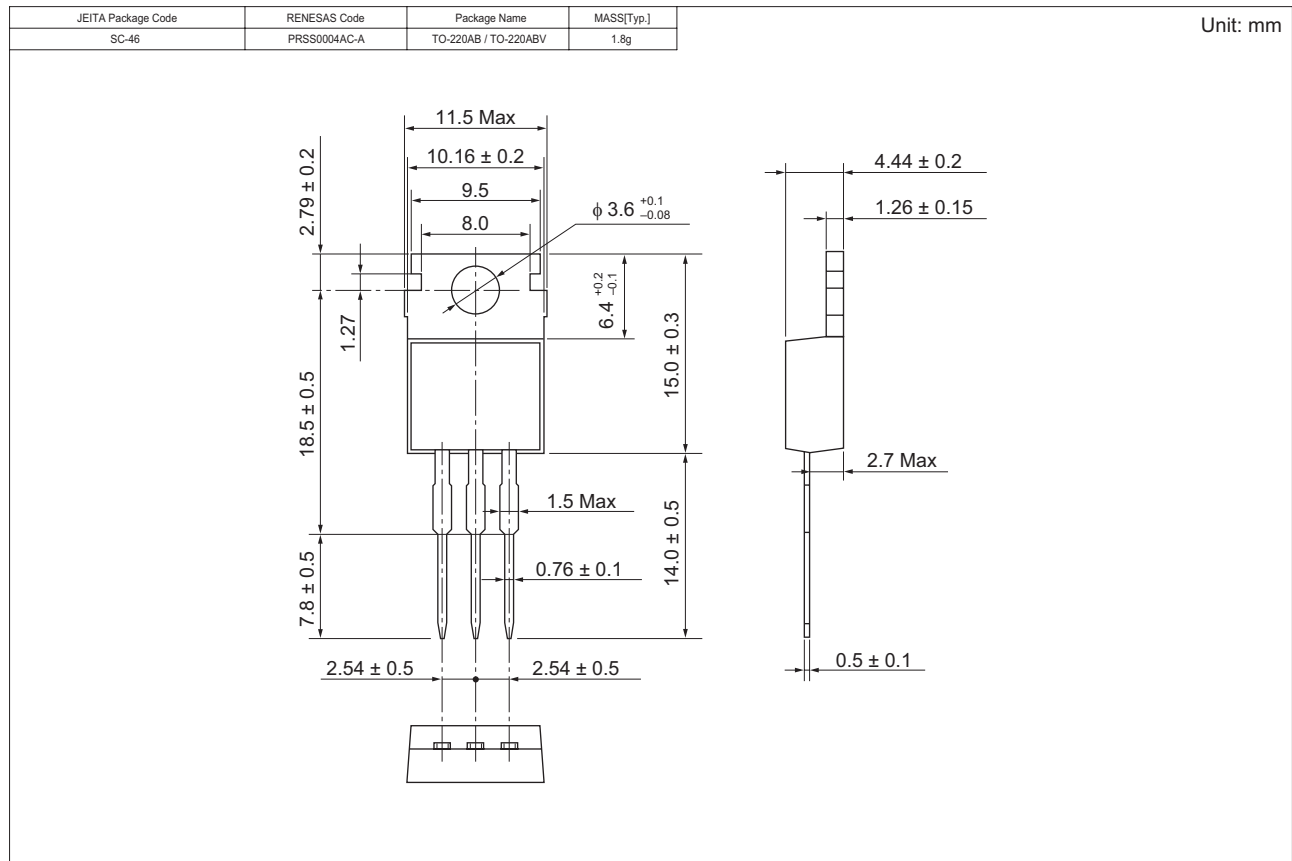
Avalanche Waveform

$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK3156-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
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Renesas Technology Hong Kong Ltd.

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Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
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Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510